an inter-layer insulating film comprising an organic material formed over said thin film transistor;

a first conductive layer formed on said inter-layer insulating film; and

a second conductive layer formed on said first conductive layer,

wherein said second conductive layer is connected to said semiconductor layer though a contact hole provided in said inter-layer insulating film.

29. The semiconductor device according to claim 28, wherein said first conductive layer is selected from the group consisting of aluminum and a material predominantly composed of aluminum.

30. The semiconductor device according to claim 28, wherein said second conductive layer is selected from the group consisting of titanium and a material predominantly composed of titanium.

31. The semiconductor device according to claim 28, wherein said organic material is an organic-based resin material predominantly selected from the group consisting of polyimide, polyimide-amide, polyamide, acrylics, and BCB (benzocyclobutane).

32. The semiconductor device according to claim 28, wherein said semiconductor device is selected from the group consisting of an active matrix liquid-crystal display device, an active matrix EL display device, and an active matrix EC display device.

33. The semiconductor device according to claim 28, wherein said semiconductor device is selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display device, a car navigation device, a personal computer, and a portable information terminal.

34. A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

an inter-layer insulating film comprising an organic material formed over said thin film transistor;

a first conductive layer formed on said inter-layer insulating film; and

a second conductive layer formed on said first conductive layer,

wherein said second conductive layer is connected to said semiconductor layer though a contact hole provided in said first conductive layer and said inter-layer insulating film.

35. The semiconductor device according to claim 34, wherein said first conductive layer is selected from the group consisting of aluminum and a material predominantly composed of aluminum.

36. The semiconductor device according to claim 34, wherein said second conductive layer is selected from the group consisting of titanium and a material predominantly composed of titanium.